




**BEST AVAILABLE COPY****Method for fabricating a phase shift mask**

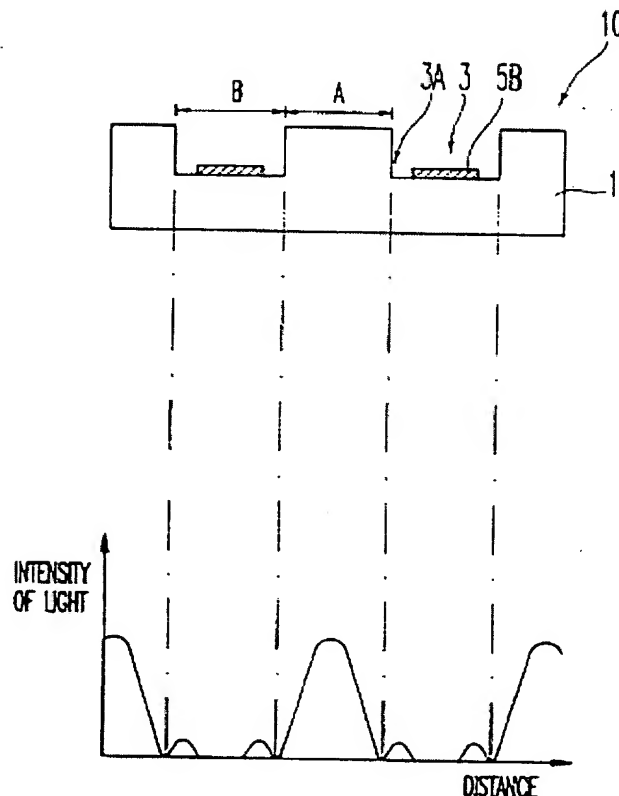
**Patent number:** CN1115412  
**Publication date:** 1996-01-24  
**Inventor:** HAM YOUNG MOK [KR]  
**Applicant:** HYUNDAI ELECTRONICS IND [KR]  
**Classification:**  
- international: G03F1/00  
- european: G03F1/00G  
**Application number:** CN19950104070 19950311  
**Priority number(s):** KR19940004785 19940311

**Also published as:**

 US5567552 (A1)  
 JP8062824 (A)  
 DE19508749 (A1)

Abstract not available for CN1115412  
Abstract of corresponding document: **US5567552**

A method for fabricating a phase shift mask is disclosed. In order to make the phase shift mask, an etching groove is formed on the light shielding portion of the quartz substrate and chrome is then formed on the center portion of the etching groove. The phase shift mask produces a phase shift effect without using phase shift materials, thereby increasing the optical contrast.



Data supplied from the **esp@cenet** database - Worldwide